

PACKAGE DIMENSIONS

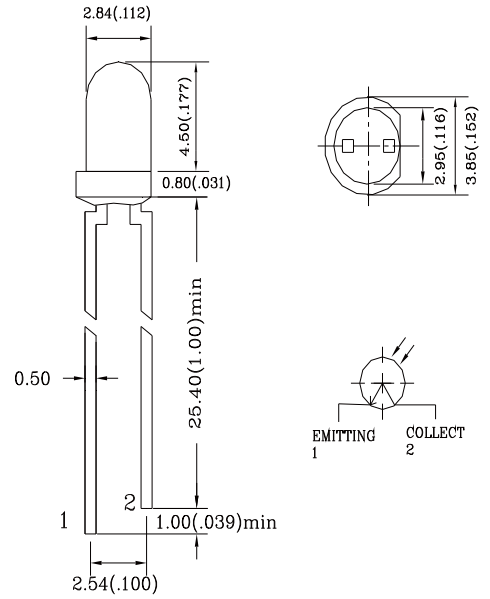
FEATURES

- * WIDE RANGE COLLECTOR CURRENTS
- * LENSED FOR HIGH SENSITIVITY
- * HIGH-OUTPUT POWER
- * HIGH-SPEED RESPONSE
- * Pb FREE PRODUCTS

CHIP MATERIALS

- * SILICON

参考資料



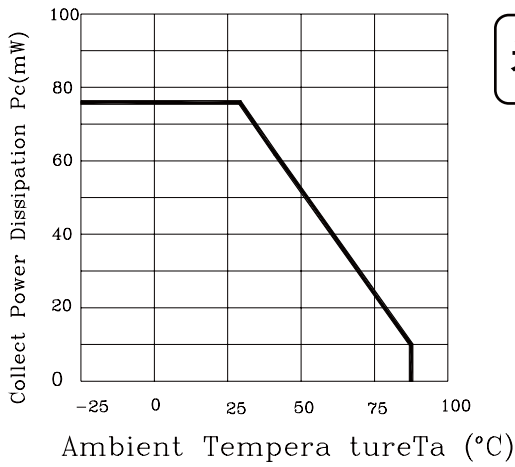
ABSOLUTE MAXIMUM RATING : (Ta = 25°C)

| SYMBOL | PARAMETER | MAX | UNIT |
|----------|-------------------------------------|---------------|------|
| PD | Power Dissipation | 10 | mW |
| V(BR)CEO | Collector-Emitter Breakdown Voltage | 30 | V |
| Topr | Operating Temperature Range | -25°C to 85°C | |
| Tstg | Storage Temperature Range | -25°C to 85°C | |

ELECTRO-OPTICAL CHARACTERISTICS : (Ta = 25°C)

| SYMBOL | PARAMETER | TEST CONDITION | MIN | TYP | MAX | UNIT |
|--------|--------------------------------------|---|-----|-------|-----|------|
| BVCEO | Collector-Emitter Breakdown Voltage | Ic = 100μA Ee = 0 mw/cm ² | 30 | | | V |
| BVECO | Emitter-Collector Breakdown Voltage | IE=100μA Ee= 0 mw/cm ² | 5 | | | V |
| ICEO | Collector Dark Current | VCE=10V Ee=0 mw/cm ² | | | 100 | nA |
| VCE(S) | Collector-Emitter Saturation Voltage | IC=2mA Ee=0.5 mw/cm ² | | | 0.4 | V |
| TR/TF | Rise / Fall Time | VCE=5V IC=1mA RL=1000Ω | | 15/15 | | uS |
| IC | On Stat Collector Current | VCE=5V Ee=0.1 mw/cm ² | | 4 | | mA |
| λp | Wavelength of Peak Sensitivity | | | 940 | | nm |

Fig. 1 Collector Power Dissipation vs. Ambient Temperature



参考資料

Fig. 2 Collector Dark Current vs. Ambient Temperature

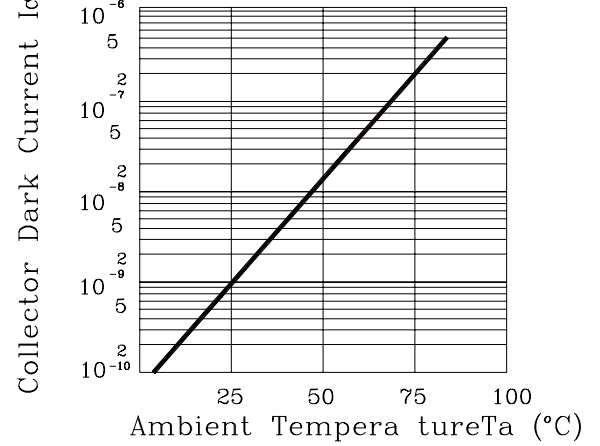


Fig. 3 Relative Collector Current vs. Ambient Temperature

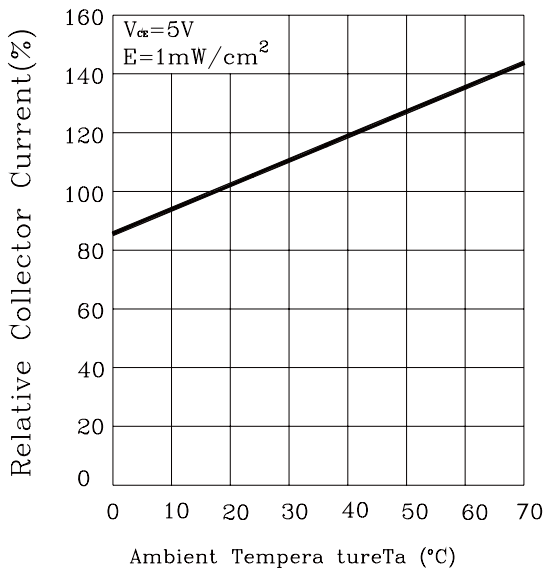


Fig. 4 Collector current vs Irradiance

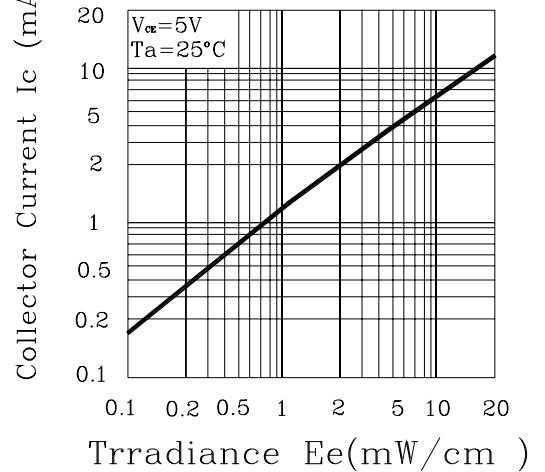


Fig. 5 Spectral Sensitivity

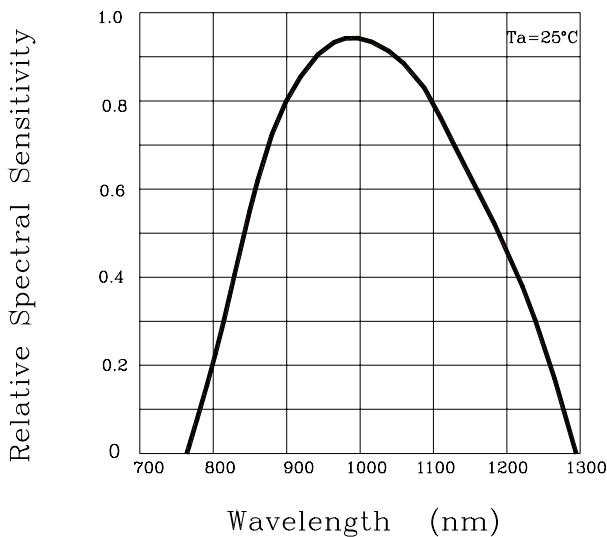


Fig. 6 Collector Current vs Collector-Emitter Voltage

